1. General description

NPN/NPN matched double transistors in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High collector current capability I_C and I_{CM}
- Reduces component count
- Reduces pick and place costs
- · Current gain matching 5%
- · Application-optimized pinout
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Current mirror
- Differential amplifier
- · Linear voltage regulators
- MOSFET drivers
- · High-side switches
- · Power management
- Amplifiers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	80	V
I _C	collector current			-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	2	Α
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 150 mA; T _{amb} = 25 °C	[1]	63	-	250	
Per device							
h _{FE1} /h _{FE2}	DC current gain matching	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$		0.95	1	1.05	
V _{BE1} -V _{BE2}	base-emitter voltage matching		[2]	-	-	2	mV

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



^[2] The smaller of the two values is subtracted from the larger value.

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B1	base TR1		04 54 50
2	B2	base TR2	<u> </u>	C1 E1 E2
3	C2	collector TR2		TR1 TR2
4	E2	emitter TR2		
5	E1	emitter TR1	TSOP6 (SOT457)	B1 B2 C2 aaa-024629
6	C1	collector TR1		-33 02 1020

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCM56DS-Q	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457

7. Marking

Table 4. Marking codes

Type number	Marking code
BCM56DS-Q	3D

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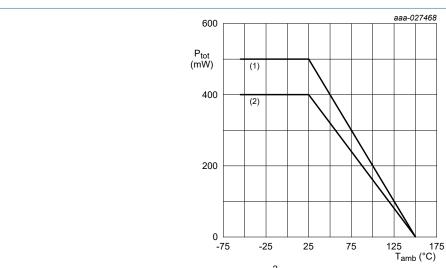
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or					
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	80	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _B	base current			-	0.2	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	0.3	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	270	mW
			[2]	-	320	mW
Per device	<u>'</u>		,	'	'	'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
			[2]	-	500	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 1 cm².



- (1) = FR4 PCB, single sided copper, 1 cm²
- (2) = FR4 PCB, single sided copper, standard footprint

Fig. 1. Per device: Power derating curves

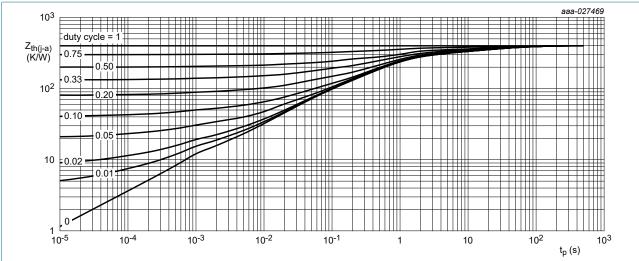
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9. Thermal characteristics

Table 6. Thermal characteristics

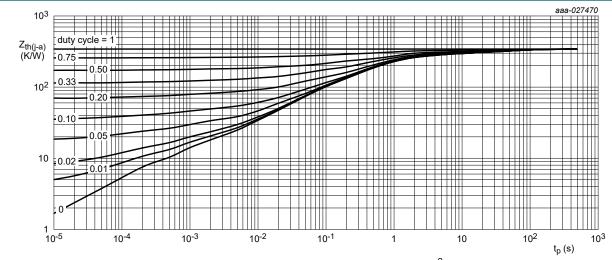
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transiste	or		'	1			
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	-	463	K/W
	junction to ambient		[2]	-	-	391	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	150	K/W
Per device	'		,	1			'
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	313	K/W
	junction to ambient		[2]	-	-	250	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².



FR4 PCB, single sided copper, tin-plated and standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single sided copper, tin-plated, mounting pad for collector 1 cm²

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A		100	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 2 mA; I _B = 0 A		80	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I _C = 0 A; I _E = 100 μA		5	-	-	V
I _{CBO} colle	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C		-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	100	nA
h _{FE} DC curi	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C		63	-	-	
		V _{CE} = 2 V; I _C = 150 mA; T _{amb} = 25 °C	[1]	63	-	250	
		V_{CE} = 2 V; I_{C} = 500 mA; T_{amb} = 25 °C	[1]	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	500	mV
V_{BE}	base-emitter voltage	V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	[1]	-	-	1	V
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	4.5	-	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C		100	155	-	MHz
Per device							
h _{FE1} /h _{FE2}	DC current gain matching	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$		0.95	1	1.05	
V _{BE1} -V _{BE2}	base-emitter voltage matching		[2]	-	-	2	mV

Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02$ The smaller of the two values is subtracted from the larger value.

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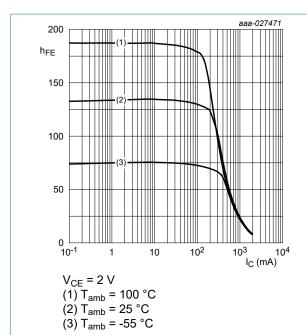


Fig. 4. DC current gain as a function of collector current; typical values

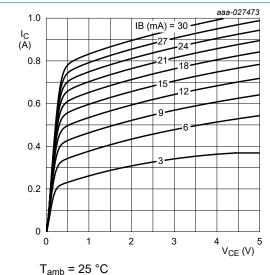


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

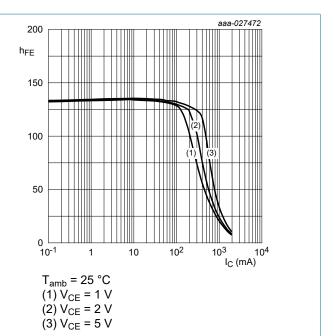
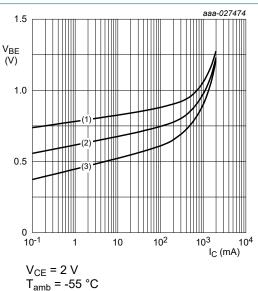


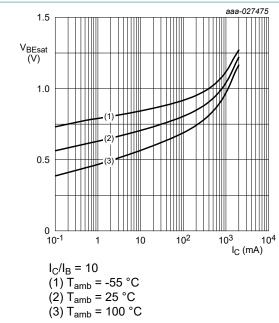
Fig. 5. DC current gain as a function of collector current; typical values



 $T_{amb} = -55$ °C $T_{amb} = 25$ °C $T_{amb} = 100$ °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values

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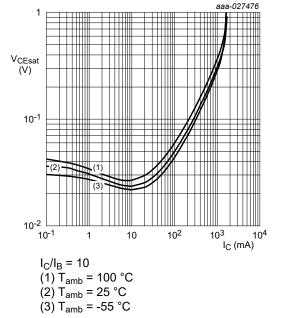
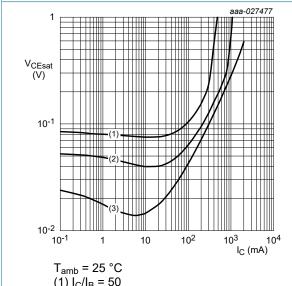
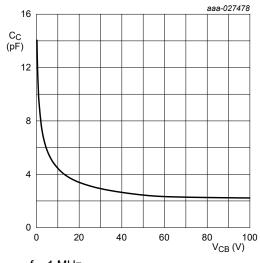


Fig. 8. Base-emitter saturation voltage as a function of Fig. 9. Collector-emitter saturation voltage as a collector current; typical values function of collector current; typical values



(1) $I_C/I_B = 50$ (2) $I_C/I_B = 20$ $(3) I_{\rm C}/I_{\rm B} = 5$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$

Fig. 11. Collector capacitance as a function of collectorbase voltage; typical values

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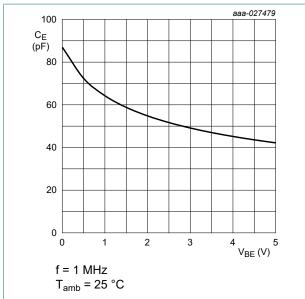


Fig. 12. Emitter capacitance as a function of emitterbase voltage; typical values

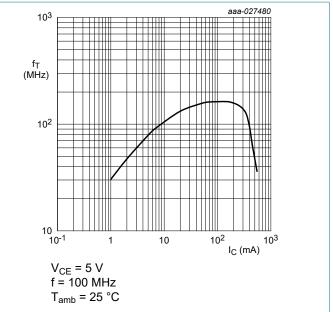


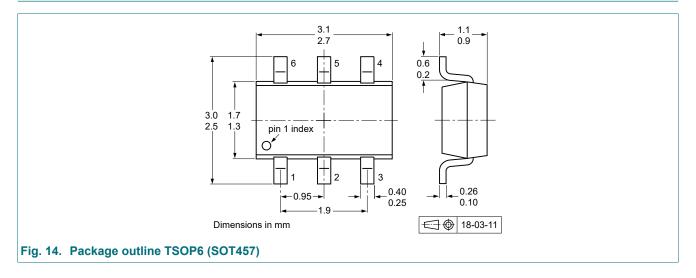
Fig. 13. Transition frequency as a function of collector current; typical values

11. Test information

Quality information

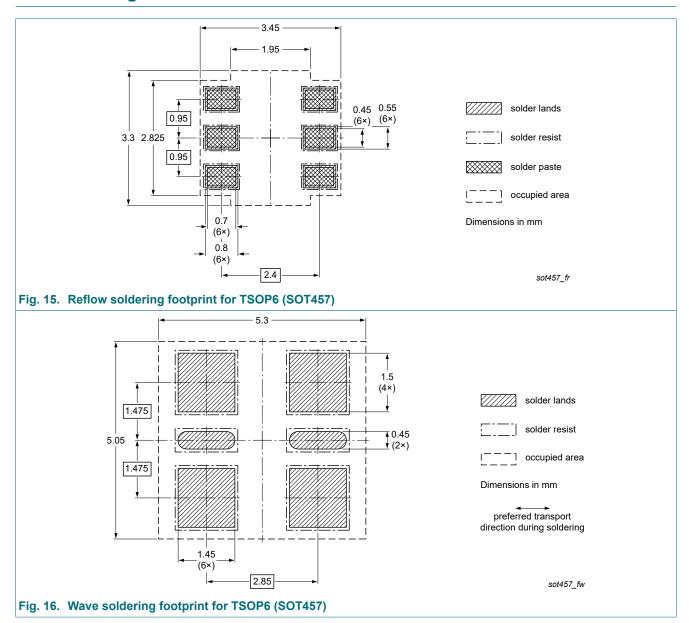
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BCM56DS-Q v.1	20241206	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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